Quarterly Financial Result (Supplementary Materials)

Quarter 2: three months ended
June 30, 2025

August 12, 2025
Code: 6871

MICRONICS JAPAN CO., LTD.

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Quarterly Financial Results (Q2)

Consolidated Result Summary

(Unit : Mils. of Yen)
*Amounts less than one million yen are rounded down

	FY12/2024	FY12/2025					
	Apr.-Jun.	Jan.-Mar.	Apr.-Jun.	QoQ		YoY	
	Q2 ⓐ	Q1 ⓑ	Q2 ⓒ	(△) ⓒ-ⓑ	(%)	(△) ⓒ-ⓐ	(%)
Net Sales	14,376	14,124	18,996	+4,872	+34.5%	+4,620	+32.1%
Probe Card	13,715	13,663	18,536	+4,872	+35.7%	+4,820	+35.1%
TE ※	661	460	460	+0	-0.1%	▲ 200	-30.4%
Gross Profit	6,735	7,614	8,787	+1,172	+15.4%	+2,051	+30.5%
Operating profit	3,255	2,857	4,711	+1,854	+64.9%	+1,456	+44.7%
Ordinary profit	3,401	2,902	4,492	+1,589	+54.8%	+1,090	+32.1%
Net Income Attributable to Owner of Parent	2,414	1,673	3,101	+1,427	+85.3%	+686	+28.4%

※ : Test Equipment

Consolidated Result Summary

(Unit：Mils. of Yen)
*Amounts less than one million yen are rounded down

	FY12/2024	FY12/2025					
	Jan.-Jun.			As of May.13		YoY	
	Previous year ⓐ	Forecast ⓑ	Results ⓒ	(△) ⓒ-ⓑ	(%)	(△) ⓒ-ⓐ	(%)
Net Sales	26,171	31,600	33,120	+1,520	+4.8%	+6,949	+26.6%
Probe Card	25,018	30,700	32,199	+1,499	+4.9%	+7,181	+28.7%
TE ※	1,153	900	921	+21	+2.3%	(232)	(20.1%)
Gross Profit	12,559	—	16,401	—	—	+3,842	+30.6%
Operating profit	5,764	7,700	7,569	(130)	(1.7%)	+1,804	+31.3%
Ordinary profit	5,806	7,600	7,394	(205)	(2.7%)	+1,588	+27.4%
Net Income Attributable to Owner of Parent	3,685	5,300	4,774	(525)	(9.9%)	+1,089	+29.6%

※：Test Equipment

Summary on Results

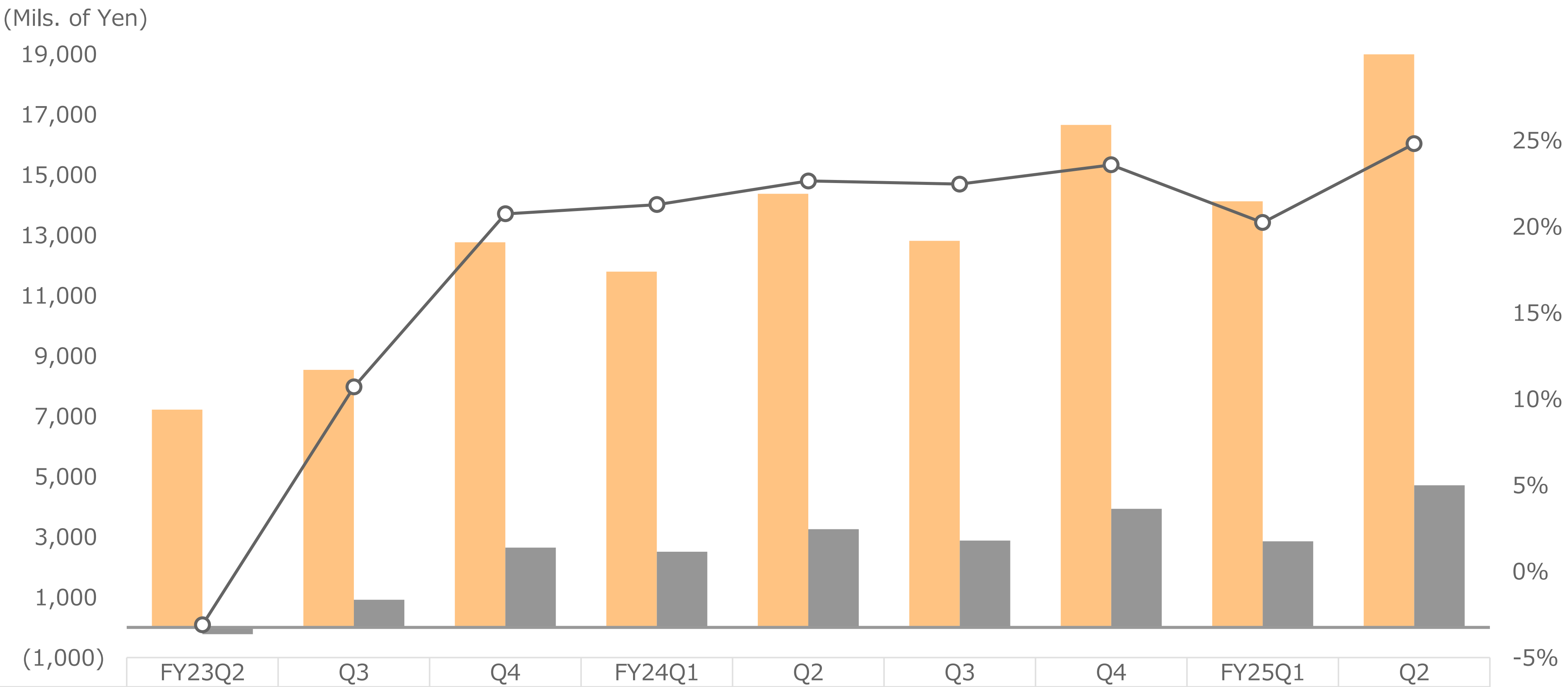
Probe card

- The sales of probe cards for memory achieved a record high, primarily for DRAM, due to some products being shifted from the previous quarter and orders brought forward from the third quarter.
- The decrease in order volume is due to a revision in the order timing because of the longer lead times for probe cards. However, the demand for HBM (High-Bandwidth Memory) remains strong.
- The sales of probe cards for non-memory applications were flat compared to the previous quarter.
- The segment profit improved compared to the previous quarter, supported by strong sales of probe cards for DRAM.

TE

- Sales remained level compared to the previous quarter, supported by steady performance in semiconductor test sockets.
- The segment reported a loss.

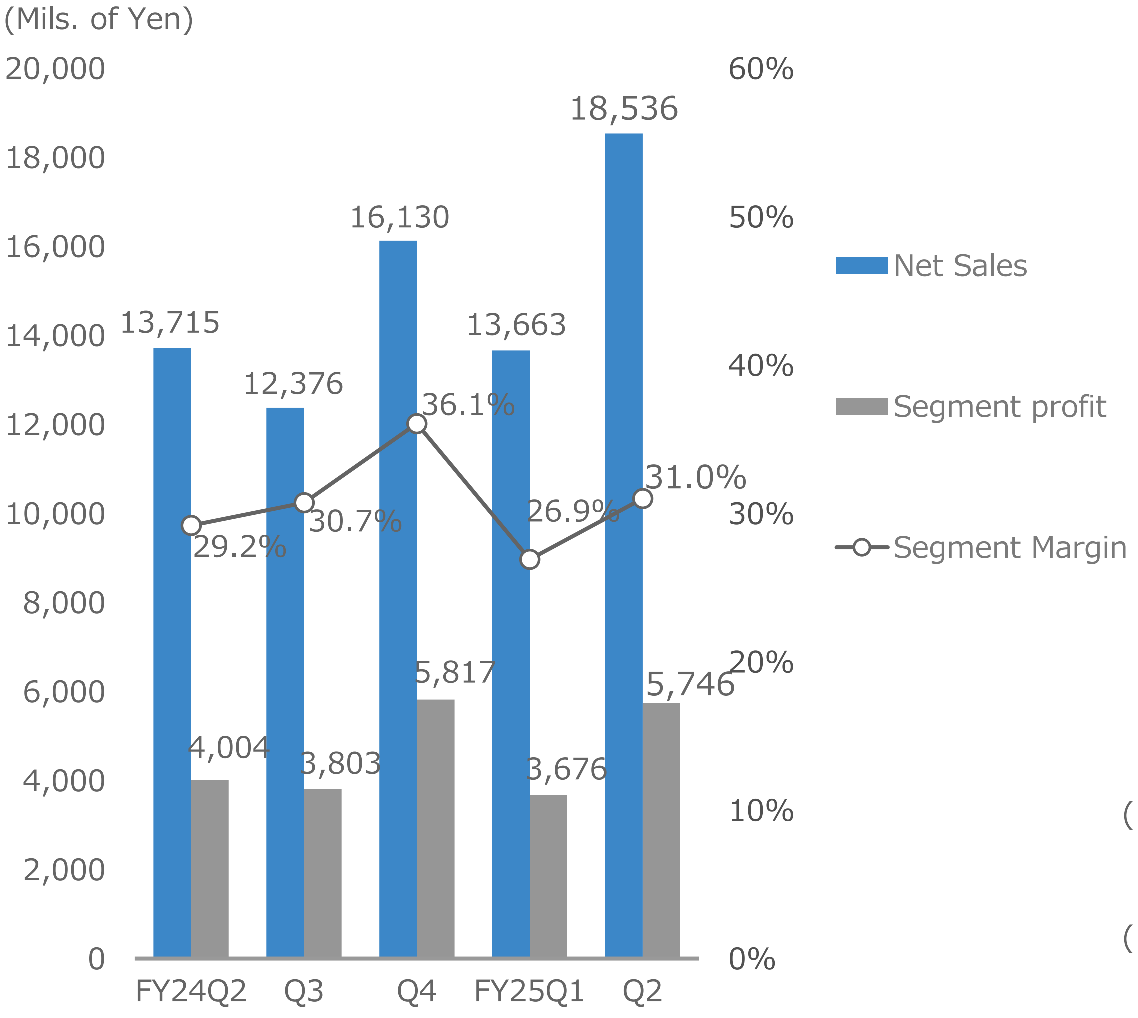
Quarterly Financial Result



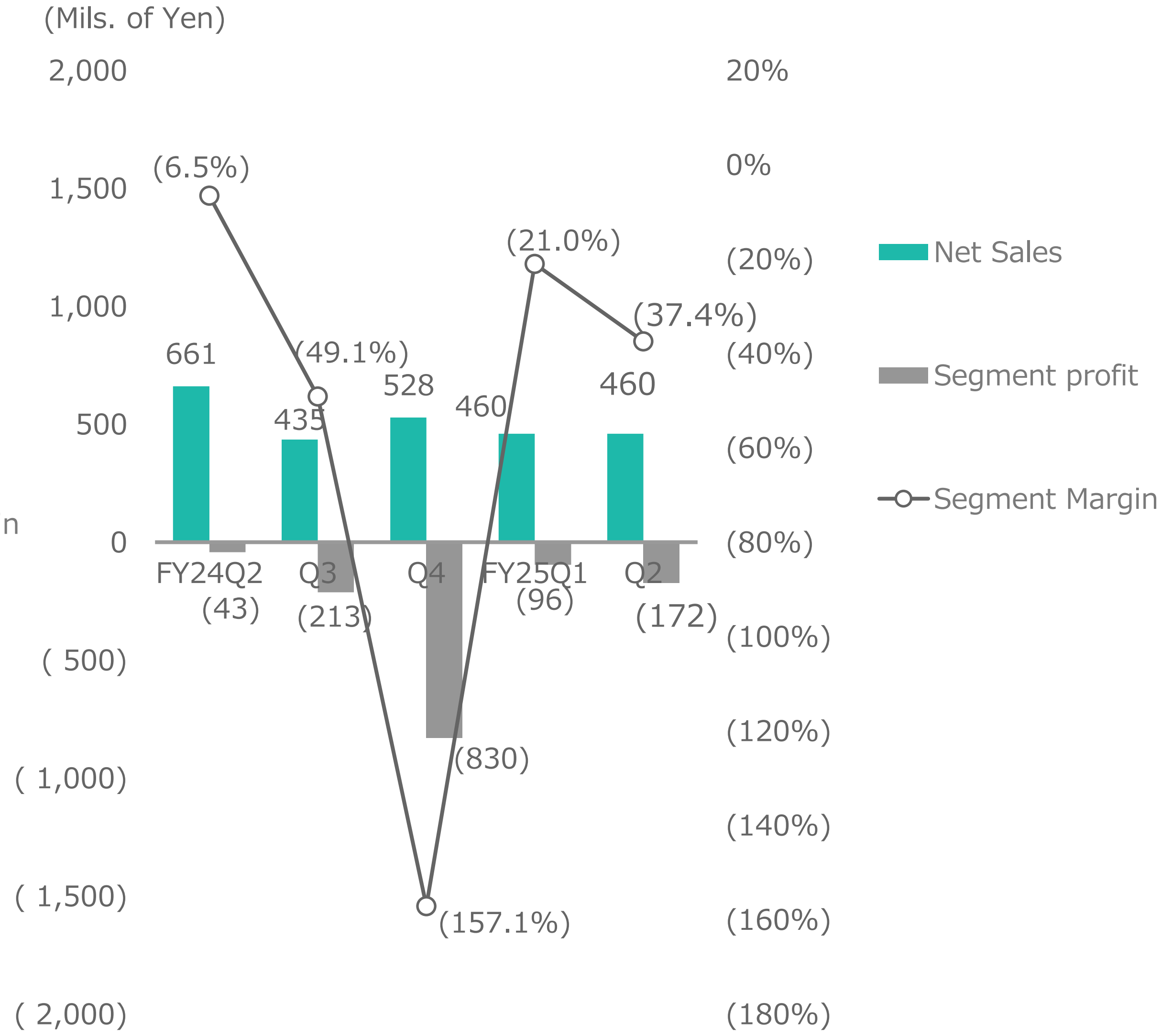
	FY23Q2	Q3	Q4	FY24Q1	Q2	Q3	Q4	FY25Q1	Q2
🟧 Net Sales	7,216	8,537	12,769	11,794	14,376	12,812	16,659	14,124	18,996
⬛ Operating profit	(224)	913	2,648	2,508	3,255	2,878	3,928	2,857	4,711
–○– Operating Margin	(3.1%)	10.7%	20.7%	21.3%	22.6%	22.5%	23.6%	20.2%	24.8%

Business Condition by Segment

Probe card

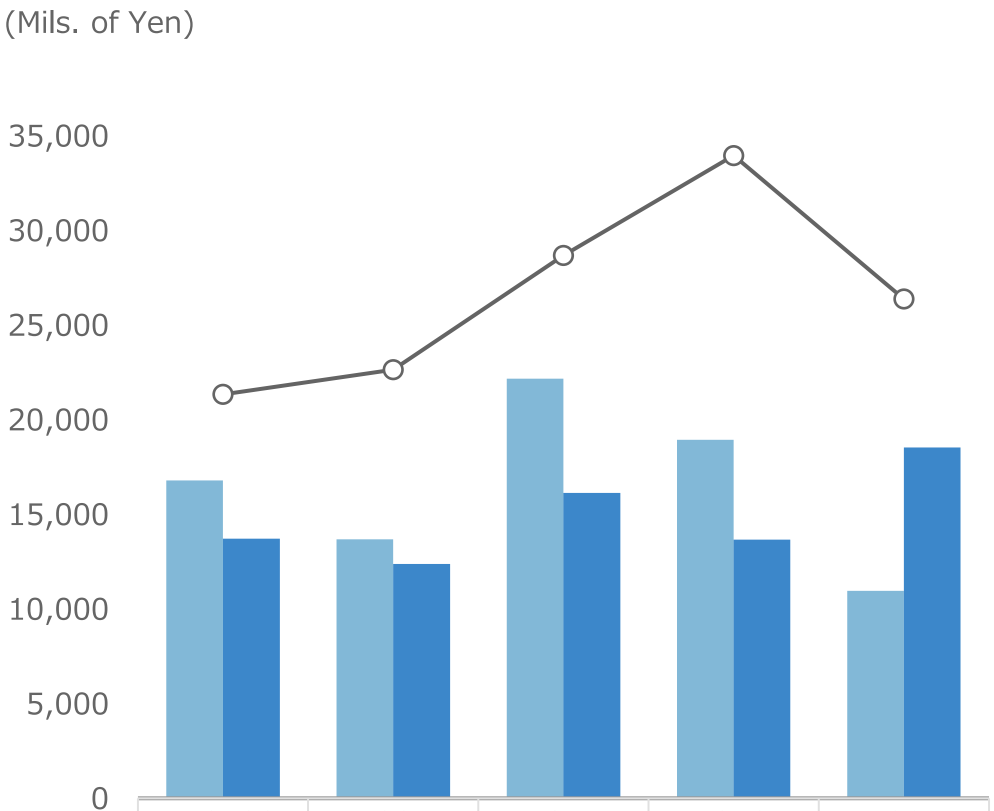


TE



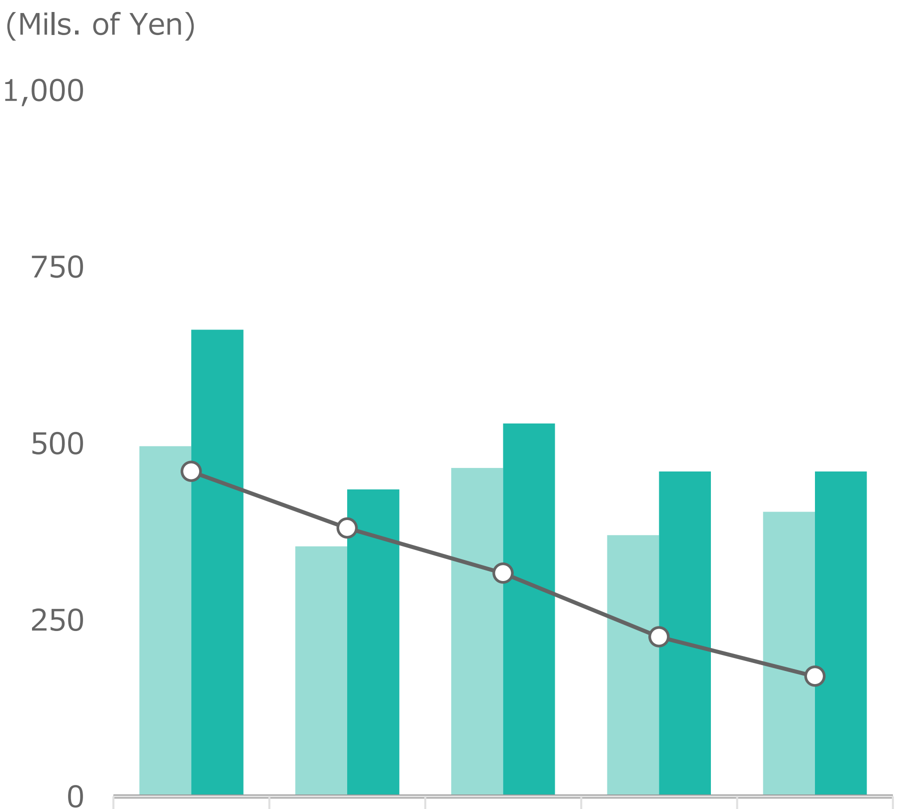
Quarterly Orders, Net Sales & Backlog

Probe card



	FY24Q2	Q3	Q4	FY25Q1	Q2
Order Received	16,792	13,684	22,165	18,943	10,955
Net Sales	13,715	12,376	16,130	13,663	18,536
Order Backlog	21,343	22,650	28,684	33,965	26,384

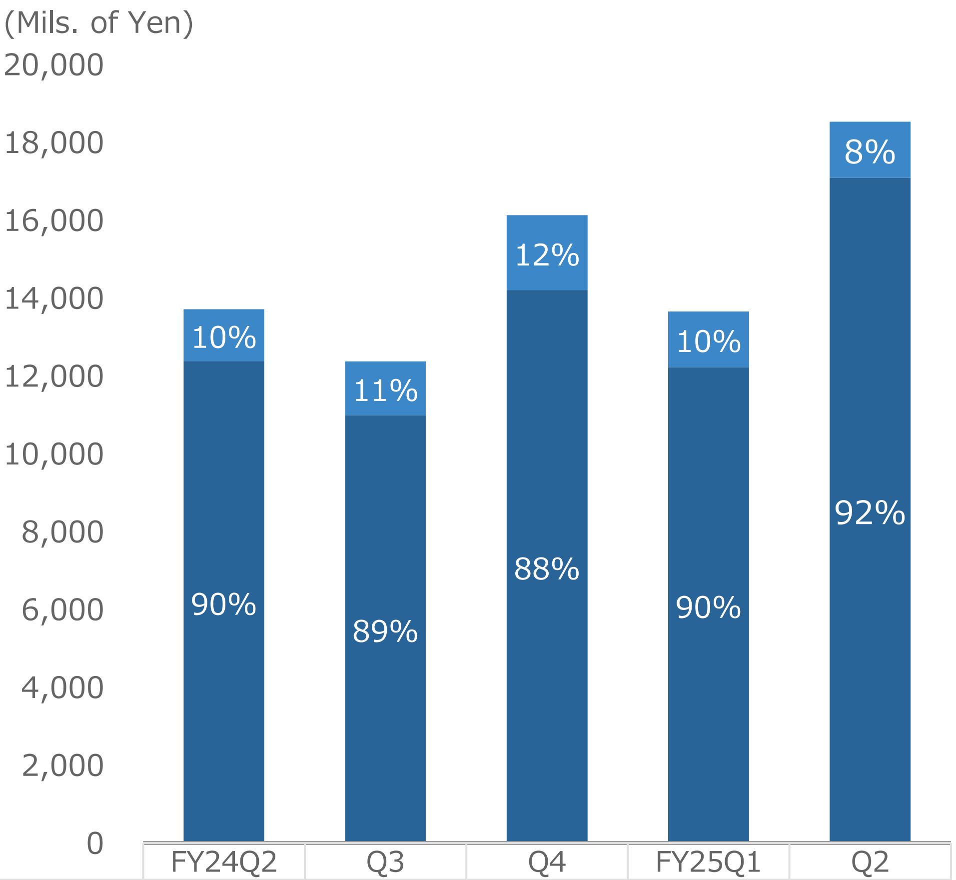
TE



	FY24Q2	Q3	Q4	FY25Q1	Q2
Order Received	496	354	465	370	403
Net Sales	661	435	528	460	460
Order Backlog	460	380	316	226	170

Quarterly Net Sales by Product

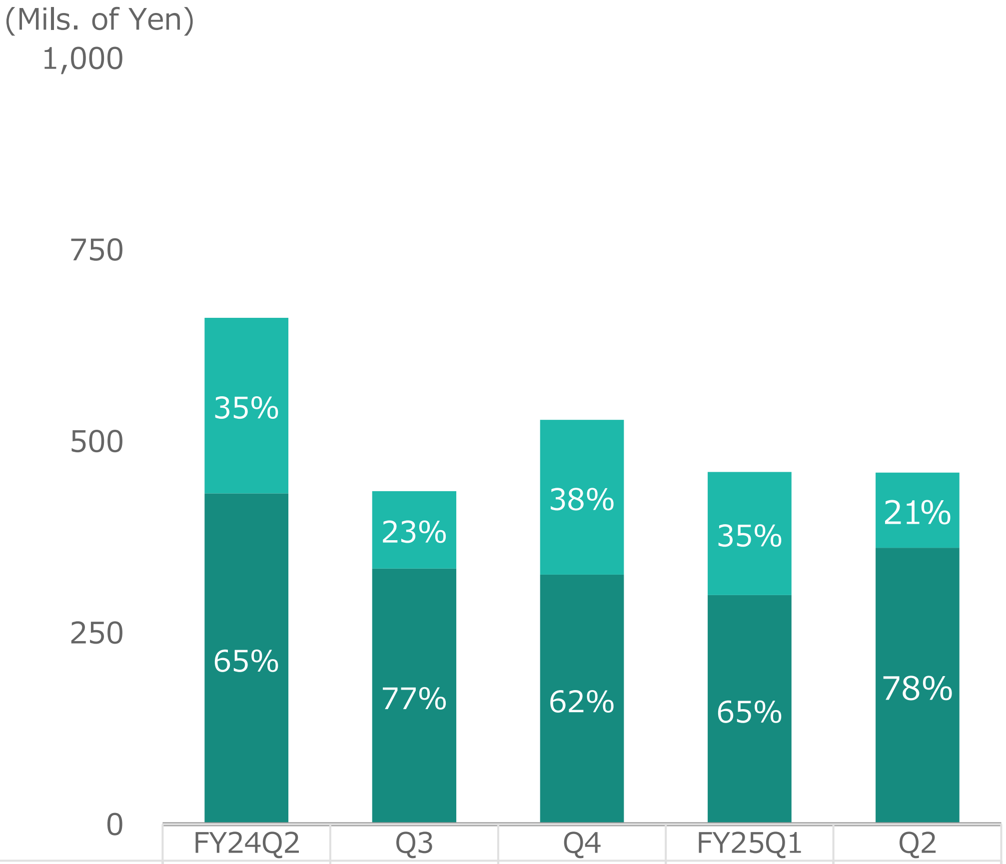
Probe card



	FY24Q2	Q3	Q4	FY25Q1	Q2
■ Non-Memory	1,328	1,381	1,924	1,432	1,437
■ Memory	12,387	10,996	14,206	12,230	17,098
total	13,715	12,376	16,130	13,663	18,536

※ Including sales of Cantilever type

TE

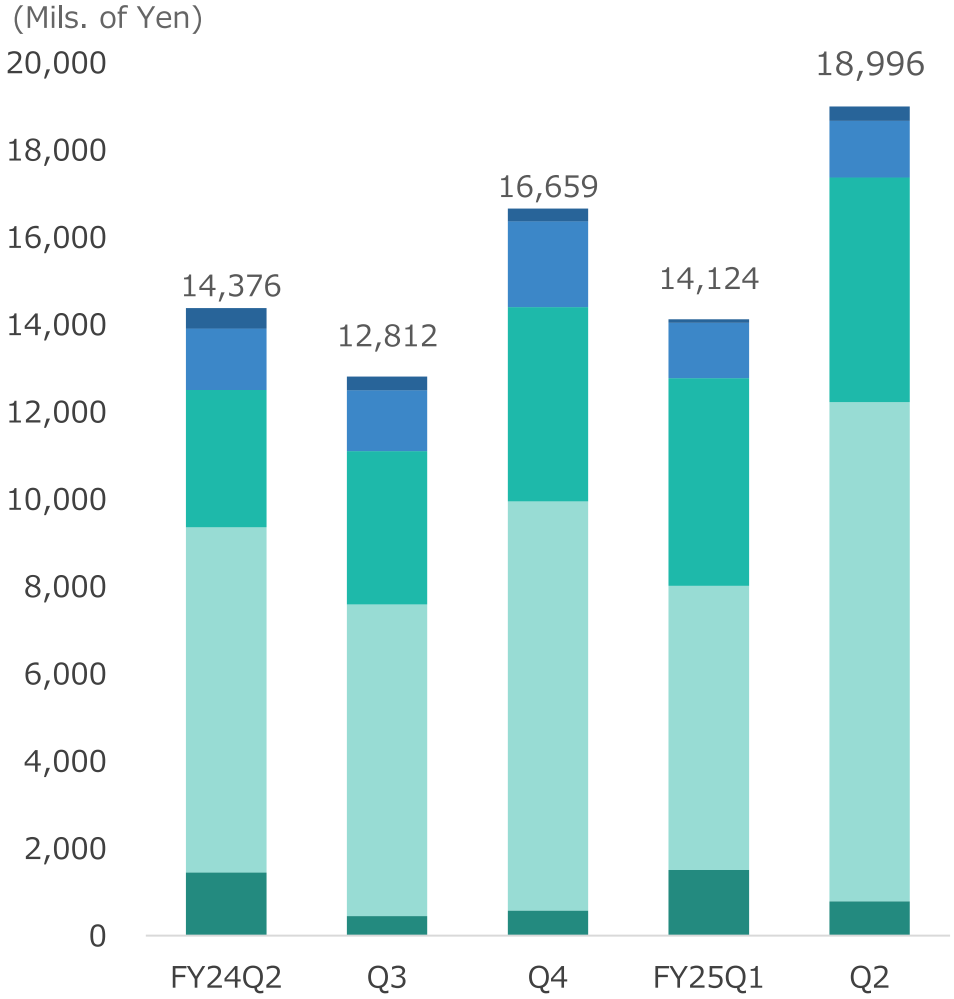


	FY24Q2	Q3	Q4	FY25Q1	Q2
■ Testing Equipment※1	229	101	202	161	98
■ Testing Device ※2	432	334	326	299	361
total	661	435	528	460	460

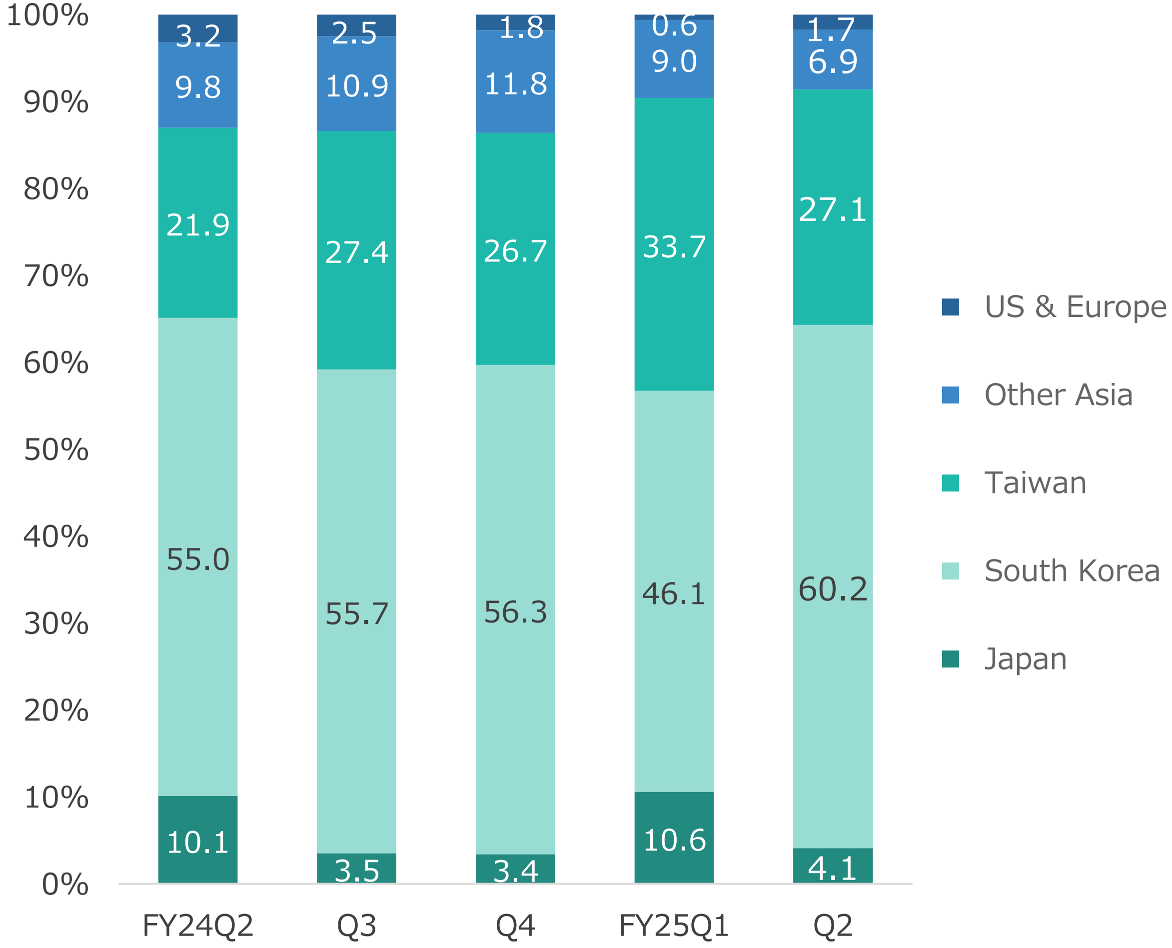
※1 Custom testers, Semiconductor probers, FPD test equipment, etc.
※2 Test sockets for semiconductors, Probe units for FPDs

Quarterly Net Sales by Region

Net Sales

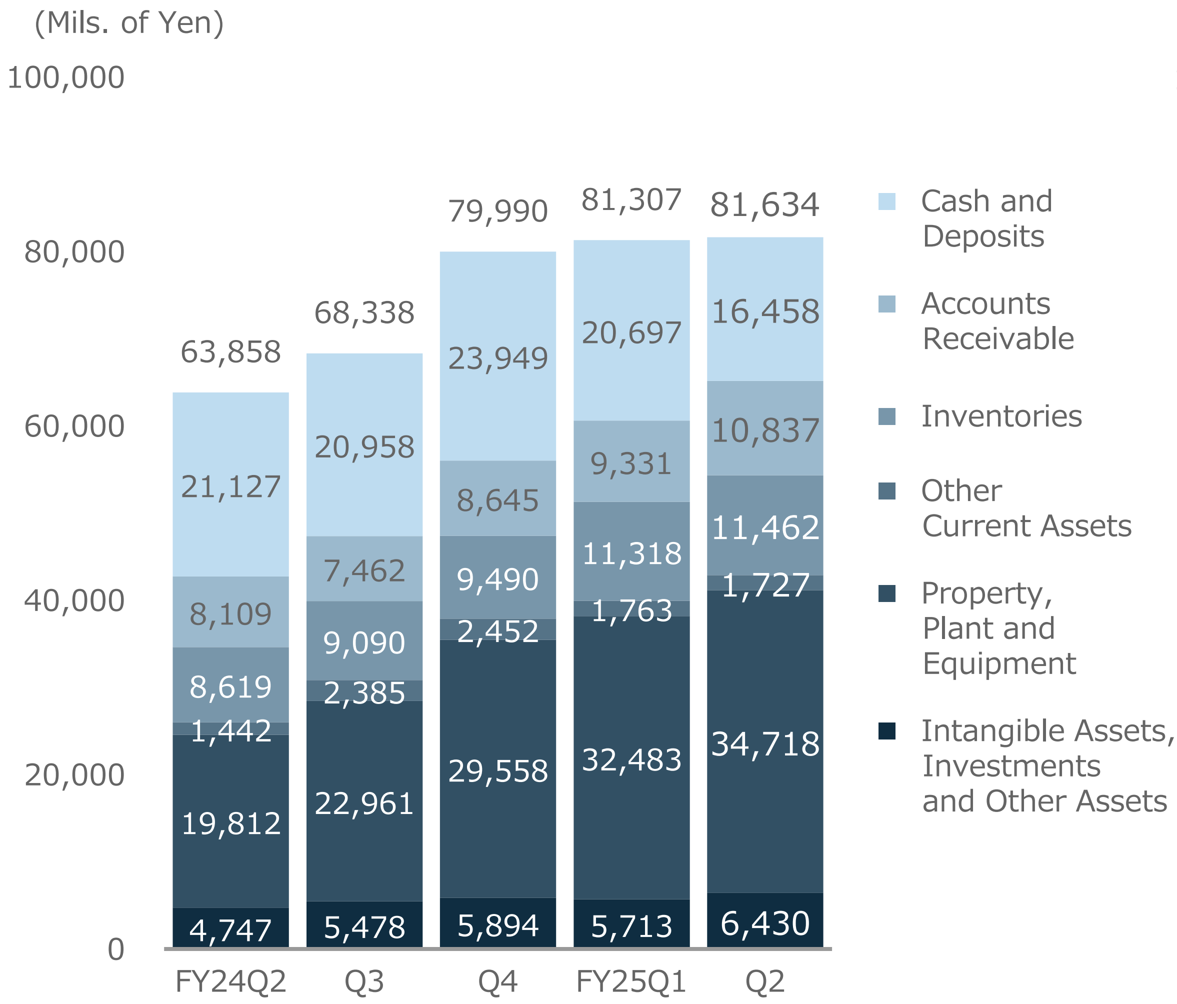


Percentage of sales

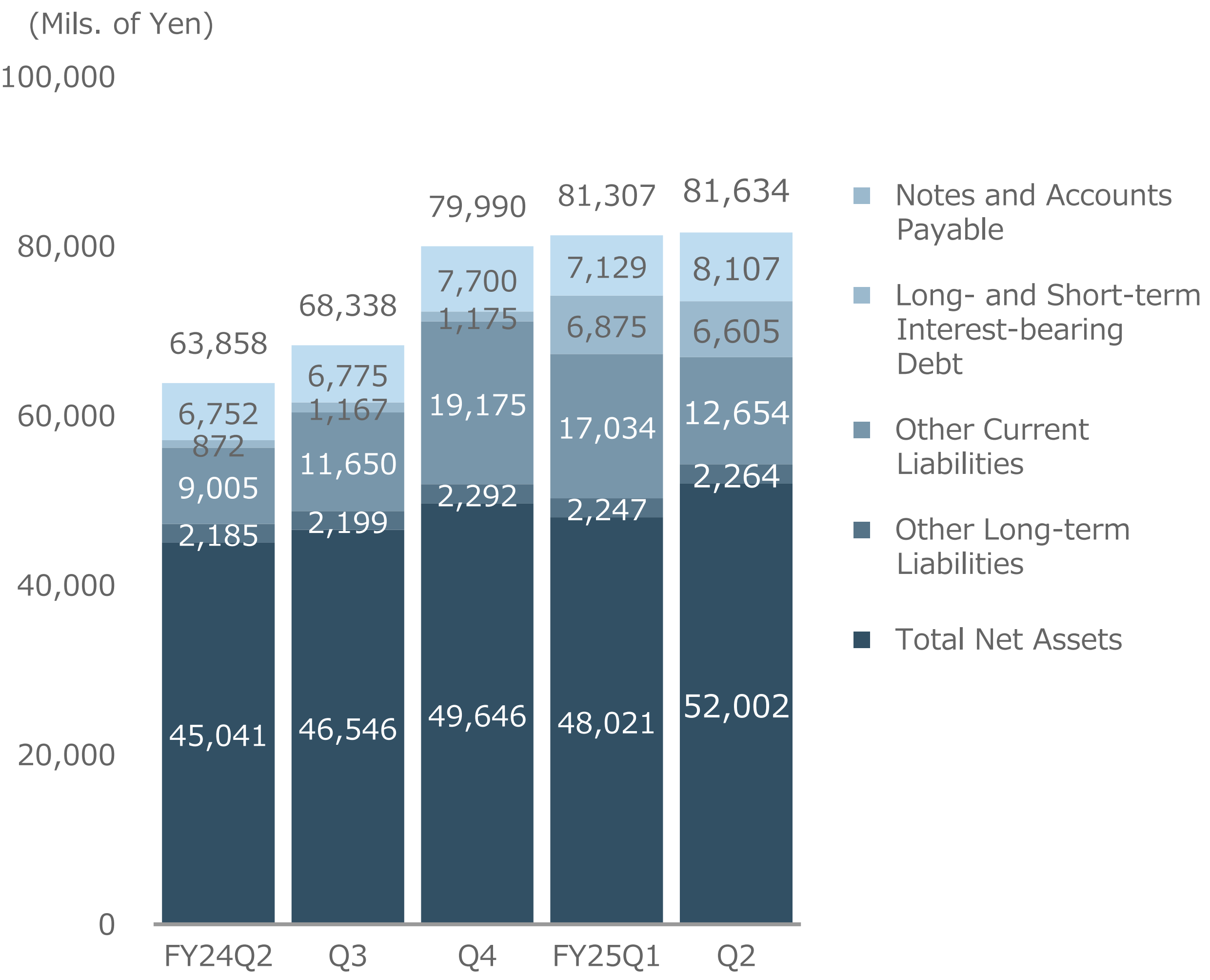


Consolidated Balance Sheet

Assets

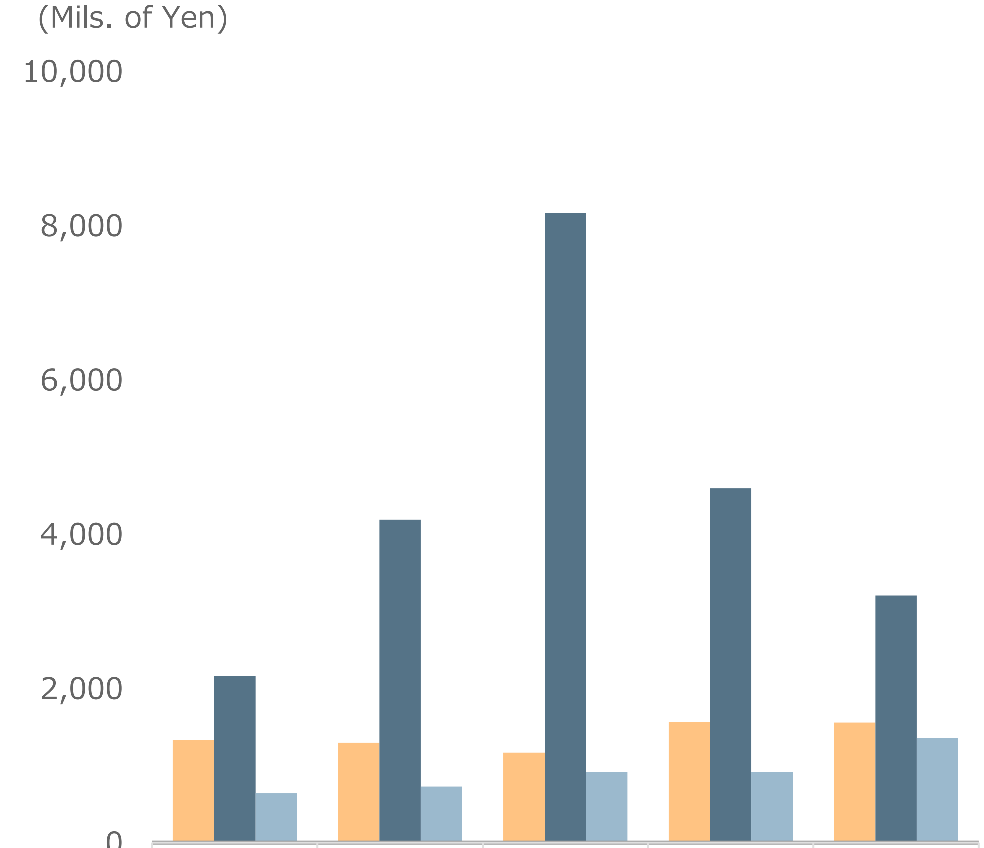


Liabilities & Net Assets



Investments/Cash Flows

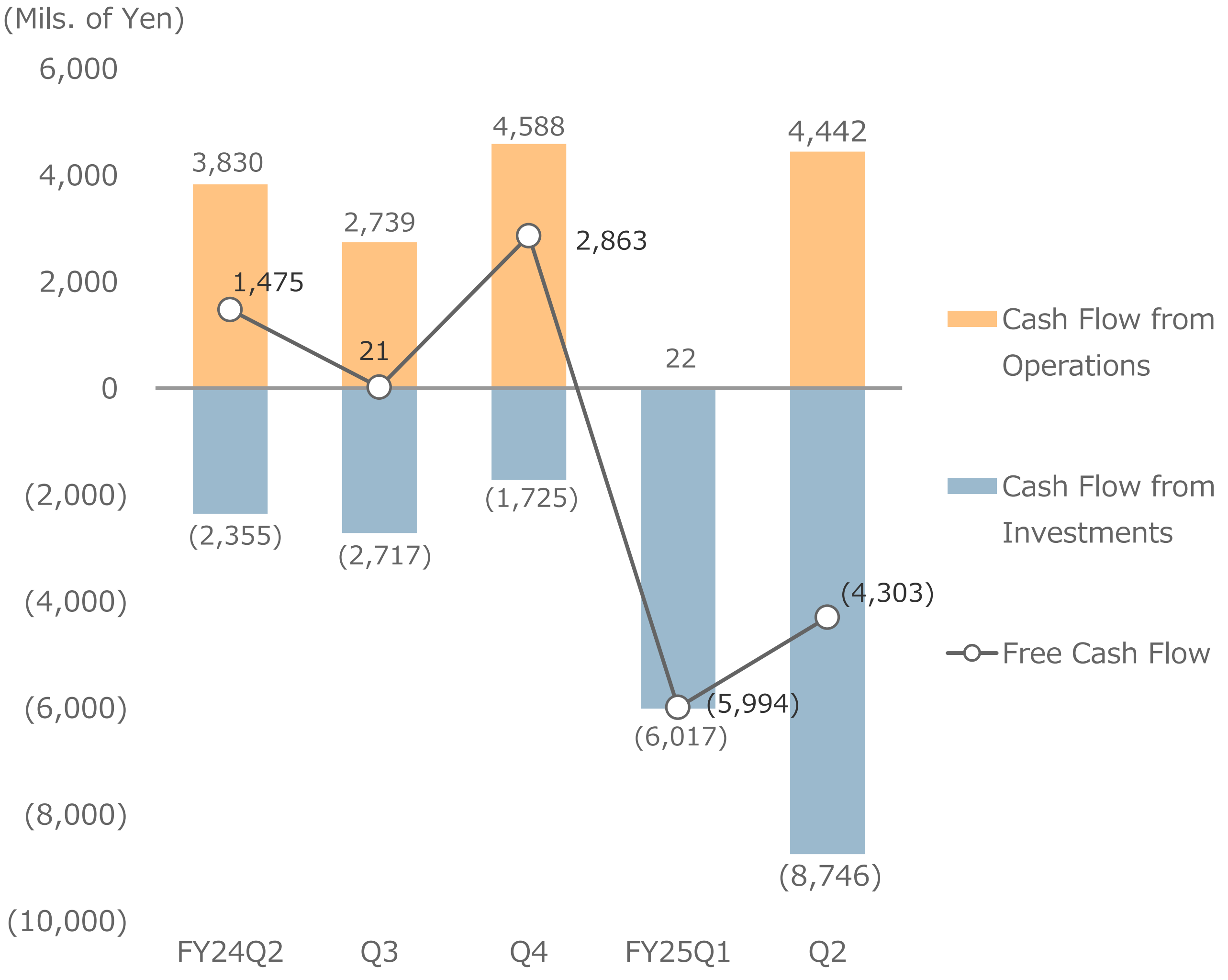
Investment,etc.



	FY24Q2	Q3	Q4	FY25Q1	Q2
■ R&D	1,331	1,295	1,168	1,564	1,555
■ CAPEX	2,158	4,188	8,161	4,592	3,203
■ Depreciation	639	727	912	914	1,355

※ Including construction in progress

Cash Flows



Forecasts

Financial Forecast

(Unit : Mils. of Yen)
*Amounts less than one million yen are rounded down

	FY12/2024	FY12/2025					
	Jan.-Sep. ⓐ	As of May.13 (Jan.-Sep.) ⓑ	Jan.-Sep. (New) ⓒ	As of May.13		YoY	
				(△) ⓒ-ⓑ	(%)	(△) ⓒ-ⓐ	(%)
Net Sales	38,983	51,000	50,000	(1,000)	(2.0%)	+11,016	+28.3%
Probe Card	37,395	49,600	48,700	(900)	(1.8%)	+11,304	+30.2%
TE	1,588	1,400	1,300	(100)	(7.1%)	(288)	(18.2%)
Operating profit	8,643	12,400	11,100	(1,300)	(10.5%)	+2,456	+28.4%
Ordinary profit	9,003	12,200	10,800	(1,400)	(11.5%)	+1,796	+20.0%
Net Income Attributable to Owner of Parent	5,746	8,500	6,800	(1,700)	(20.0%)	+1,053	+18.3%

- FX rate assumption for FY12/2024: JPY 147.00 to USD, JPY 0.10 to KRW

Financial Forecast

- A malfunction occurred in specific equipment at the existing factory for memory probe cards, causing delays in product shipments. As a result, we have factored in the anticipated impact on sales revenue for the third and fourth quarters.
- We have already identified the cause of the malfunction and implemented measures to prevent recurrence.

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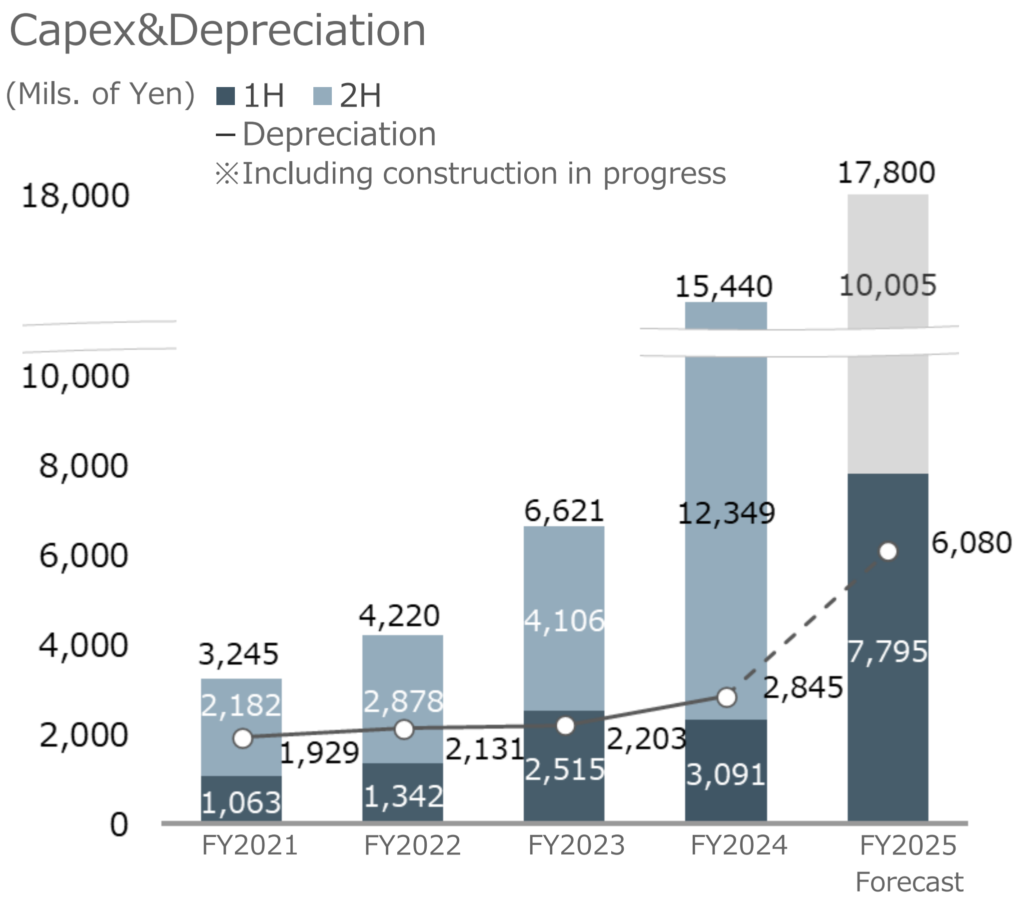
	FY12/2024	FY12/2025		
	Jan.-Dec. (Previous year) ⓐ	Jan.-Dec. (New) ⓑ	YoY	
			(△) ⓑ-ⓐ	(%)
Net Sales	55,643	68,900	+13,256	+23.8%
Probe Card	53,526	67,100	+13,573	+25.4%
TE	2,116	1,800	(316)	(15.0%)
Operating profit	12,572	13,800	+1,227	+9.8%
Ordinary profit	12,250	13,300	+1,049	+8.6%
Net Income Attributable to Owner of Parent	8,811	9,200	+388	+4.4%
Dividend（Yen）	70	72	+2	+2.9%

- FX rate assumption for FY12/2025: JPY 147.00 to USD, JPY 0.10 to KRW

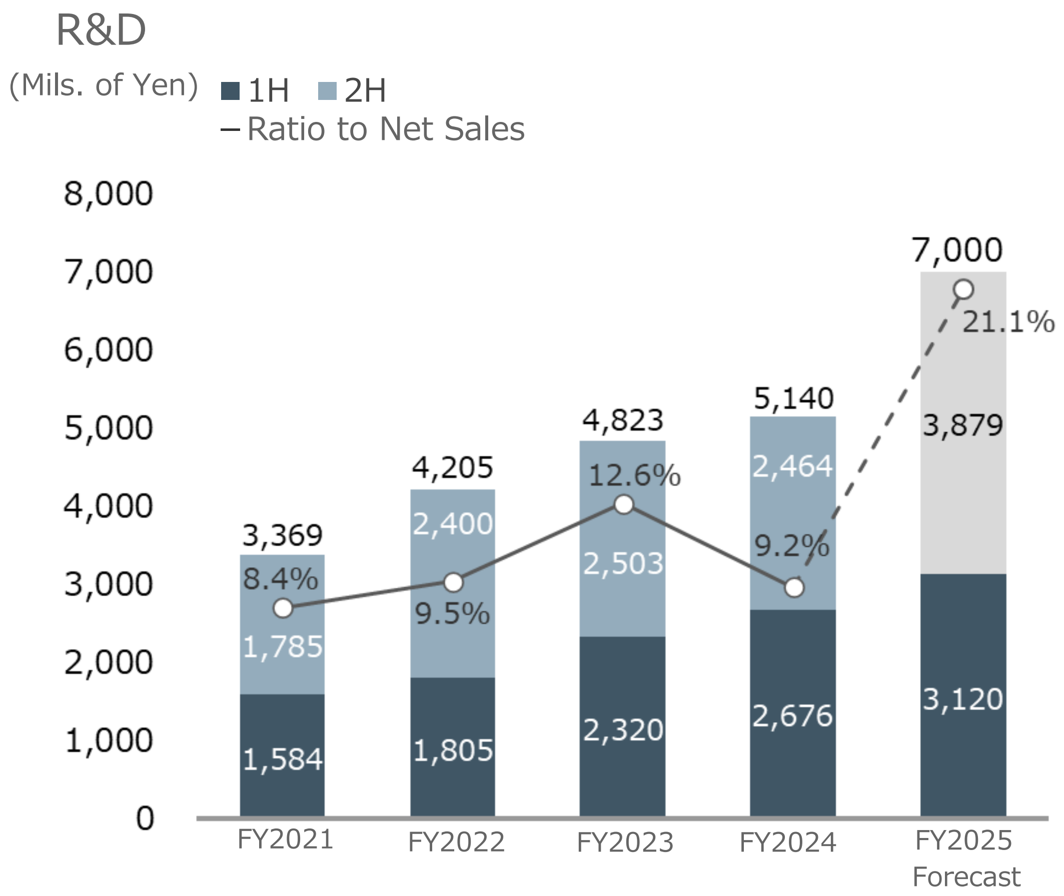
Forecasts for R&D, Capex and Depreciation

Proactive investments aimed at expanding medium- to long-term demand and continued research and development to respond to semiconductor technological innovations.

- Investment in the introduction of production equipment for the new building at the Aomori plant.
- Development of Next-Generation Technologies for Non-Memory and Memory Probe Cards.
- Development of new semiconductor-related products and expansion of applications in the TE business.


Capex&Depreciation

※Including construction in progress


R&D

Glossary and Main Products

Glossary

Wafer: Circular crystalline silicon (Si) or gallium arsenide (GaAs) sliced into a thin disk substrate used for semiconductor electrical circuits.

Chip/Die: Dies and chips are small semiconductor devices.
A semiconductor wafer is diced into many pieces, and each of these pieces is called a die or chip.

IC: Integrated circuit.

Memory IC: An integrated circuit made out of millions of capacitors and transistors that can store data such as DRAM, NAND Flash and etc.

Logic IC: An integrated circuit that performs logic functions.

DRAM: Dynamic random access memory.
A type of volatile memory with a wide range of uses including main storage for computers and general-purpose memory.

NAND-Type Flash Memory: A type of non-volatile memory that cannot be deleted even when the external power supply is interrupted. Used for USB memory, digital camera memory cards, mobile music players and mobile phone memory. Created by Toshiba in 1987.

LSI: Large-scale integrated circuit.
Called VLSI or ULSI when the transistor’s degree of integration is increased.

Micro Computer: An IC that integrates memory and a microprocessor for arithmetic processing on one chip. Recently, the word “microcomputer” is often used to refer to those incorporated in home appliances or other products for electronic control.

System on Chip (SoC) / System LSI: Large-scale IC containing nearly an entire system on one chip. Combines multiple functions previously spread across multiple ICs onto one chip. Realizes small, high-performance machinery. Mainly used in processors and memory, input/output, interface and telecommunications circuitry.

Flip Chip: Flip chips have bump electrodes on the chip surface for the purpose of high-density surface mounting of IC chips on circuit boards. The bumps and wiring board terminals are connected with solder or conductive adhesive.

Bump: Bumps are solder bumps formed on IC pads. Bumps are normally formed with gold (Au) or solder and are used primarily in flip chips for connection to substrates.

Bonding Pad: Supply of power voltage to the chip and signal exchanges with exterior are normally conducted through the lead. The bonding pads are metal electrodes around the chip connecting this lead with each terminal on internal circuitry.

IoT: Internet of Things, allowing physical devices to be sensed or controlled remotely across existing internet infrastructure.

FPD: Flat panel display.

LCD: liquid crystal display.

Glossary

Wafer Test / Probe Test: An electrical test conducted by placing a probe needle on a wafer chip bonding pad.

Final Test / Package Test: Electrical testing of assembled ICs.

DUT: Device under test.

Area Array: A state which has test pads in a grid array on the surface of a chip.

Cantilever Probe Card: Also called a cantilever needle. A probe card using a one-sided needle probe as a fulcrum. Shaped by hand.

Advanced Probe Card: Probe cards other than the cantilever type.

Vertical Probe Cards: A vertical probe card is a probe card in which probe needles are vertical to the substrate. Vertical probe cards are suitable for area array, small pad, low voltage, low needle pressure, and high frequency measurement.

MEMS: Micro-Electro-Mechanical Systems.

MEMS Type Probe Card: MEMS type probe cards are probe cards using MEMS technology. They have a structure that allows the mechanical movement of probe terminals.

DFT: Design for testability

BIST: Built In Self Test

AI(Artificial Intelligence): The simulation of human intelligence processes by machines. It generally needs various type of semiconductors like image sensors.

Generative AI: automatically creates diverse content, including images, videos, and text. It learns from extensive pre-analyzed data, enabling the generation of new content. High-performance semiconductors like GPUs or HBMs are crucial for effective generative AI.

GPU (Graphics Processing Unit):A semiconductor chip that handles complex data calculations, including 3D graphics processing. It excels in parallel computing. When combined with HBM, it enables even faster performance, especially for generative AI.

HBM (High Bandwidth Memory) : A type of DRAM known for its wide bandwidth and high-power efficiency. By stacking DRAM chips and connecting them to a processor using multiple buses, it achieves fast and large-capacity data transfer. It is primarily packaged with GPUs/CPU and used in HPCs and AI servers.

HPC(High Performance Computing) : A technology that performs complex computational processing on massive data at high speeds. It uses high-performance processors to handle big data efficiently.

General-purpose server : A computer or program that performs necessary processing through a network in response to requests from users.

AI server: A specialized server designed specifically for training and inference of generative AI. It is equipped with powerful CPUs, GPUs, HBM, and other devices, providing higher computational capabilities, large memory storage, high bandwidth, and low latency.

Data center :A facility designed to securely store servers and network equipment. When investments in data centers increase, there is often a higher demand for general-purpose servers, which in turn can lead to an increased need for DRAM chips.

Our Products

Probe Cards

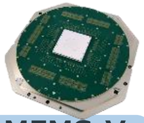
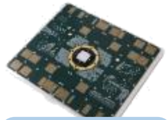
U-Probe: Our core product, realizing the world’s first wafer-scale probing created with MJC’s proprietary MEMS probe “micro-cantilever” and global top-level thin-film multilayer technology. With a bare minimum of contacting times via a crescent arrangement for DRAM, this product is currently the industry standard. Mainly used for memory testing on DRAM and flash memory.

SP-Probe: Vertical spring pin-type probe card suitable for 12-inch wafer batch measurements. Mainly used for testing NAND flash memory.

MEMS-V / Vertical-Probe: Vertical needle-type probe card used for testing highly integrated, high-speed multi-pin logic devices. Provides flexible support for a variety of pad and fine pitch arrangements and is suitable for multiple individual simultaneous measurements during testing of SoC and other advanced logic devices.

MEMS-SP: Probe card used for MEMS probe developed for testing SoC devices and other flip chip-type logic devices.

Main Applications for MJC Probe Card Products

	Memory		Logic
	DRAM	Flash	SoC
Vertical		 SP-Probe	 Vertical-Probe  SP−Probe
MEMS	 U-Probe		 MEMS-V  MEMS-SP

Test Equipment

Semiconductor Tester: A system that gives electrical signals to a semiconductor device to compare output signals with expected values.

Wafer Prober: A system that handles the wafer to make contact in the designated position on the device.

Test Socket: In the final inspection of semiconductor manufacturing, a fixture is used to electrically connect the packaged device and tester. There are two types: ‘J-Contacts,’ suitable for high-frequency and high-performance devices, and ‘BeeContacts,’ which have a unique spring probe structure with excellent contact stability.

Probe Unit: Probe card with a built-in LCD prober. This blade-type unit developed by MJC is an industry standard.

MJC YOUR Best Partner, MJC Anytime Anywhere

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